

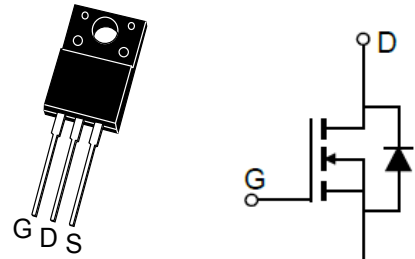
Features

- Wide Bandgap SiC MOSFET Technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed Switching
- Low Reverse Recovery (Qrr)
- Easy to Parallel and Simple to Drive
- Robust against Parasitic Turn on Even 0V Turn off Gate Voltage

Parameter		Value	Unit
V_{DS}		650	V
$R_{DS(on)}$ _typ.	$V_{GS}=18V$	250	mΩ
I_D		11	A

Benefits

- Reduced Switching Losses
- Increased System Switching Frequency
- Increased Power Density
- Reduction of Heat Sink Requirements
- Reduced EMI



ITO-220AB

Application

- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power Applications



Maximum ratings at $T_j=25^{\circ}\text{C}$, Unless otherwise specified

Parameter	Symbol	Test Condition	Value	Unit
Drain to Source Voltage	V_{DS}	$V_{GS} = 0V, I_D = 500\mu A$	650	V
Gate to Source Voltage	V_{GS}	Absolute maximum values	-10/+22	V
Recommended Operation Voltage of Gate to Source	V_{GSop}	Recommended operational values	0/+18	V
Continuous Drain Current	I_D	$V_{GS}=15V, T_C=25^{\circ}\text{C}$	11	A
		$V_{GS}=15V, T_C=175^{\circ}\text{C}$	9	
Pulsed Drain Current	I_{DM}	$V_{GS}=15V, T_C=25^{\circ}\text{C}$	22	A
Power Dissipation	P_{tot}	$T_C=25^{\circ}\text{C}, T_j=175^{\circ}\text{C}$	38	W
Operating and Storage Temperature	T_j, T_{stg}		-55 to +175	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value			Unit
		Min.	Typ.	Max.	
Thermal Resistance from Junction to Case	$R_{th(j-c)}$	-	4.00	-	$^{\circ}\text{C/W}$

Electrical Characteristics

Static Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=500\mu A$	650			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=1.8mA$	2.7		4.5	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=650V, T_j=25^{\circ}\text{C}$	-		10	μA
Gate to Source Leakage Current	I_{GSS+}	$V_{GS}=22V, V_{DS}=0V$	-		250	nA
	I_{GSS-}	$V_{GS}=-10V, V_{DS}=0V$	-		-250	
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=15V, I_D=5A$	-	380	500	m Ω
		$V_{GS}=15V, I_D=5A, T_j=175^{\circ}\text{C}$		325		
		$V_{GS}=18V, I_D=5A$	-	250	380	
		$V_{GS}=18V, I_D=5A, T_j=175^{\circ}\text{C}$		270		



Dynamic Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=500V, f=1MHz,$ $T_j=25^{\circ}C$		254		pF
Output Capacitance	C_{oss}			20.2		
Reverse Transfer Capacitance	C_{rss}			2.4		
Total Gate Charge	Q_g	$V_{GS}=0/15V, V_{DS}=500V, I_D=5A,$ $T_j=25^{\circ}C$		21.3		nC
Gate-Source Charge	Q_{gs}			6.7		
Gate-Drain Charge	Q_{gd}			11.5		
Gate Resistance	R_g	$V_{AC}=25mV, f=1MHz$		14.3		Ω

Switching Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=0/15V, V_{DD}=500V, I_D=5A,$ $R_g=10\Omega$		24		ns
Rise Time	t_r			42		
Turn-Off Delay Time	$t_{d(off)}$			26.8		
Fall Time	t_f			76		

Reverse Diode Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=3A, T_j=25^{\circ}C$	-	4.5		V
Continuous Diode Forward Current	I_S	$V_{GS}=0V, T_j=25^{\circ}C$		11		A
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_{SD}=5A,$ $V_R=500V, di/dt=530A/us,$ $T_j=25^{\circ}C$		17.8		ns
Reverse Recovery Charge	Q_{rr}			33.7		nC
Peak Reverse Recovery Current	I_{rrm}			3.5		A



Typical Performance

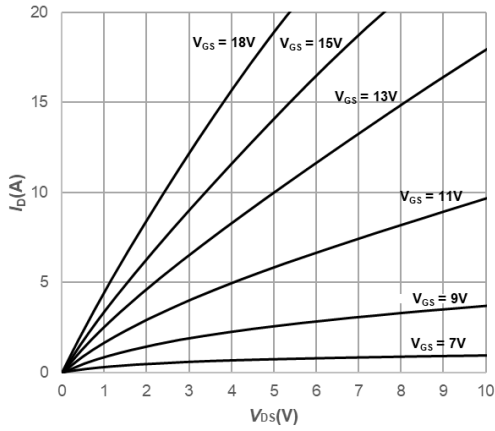


Fig1. Output Characteristics $T_j = 25^{\circ}\text{C}$

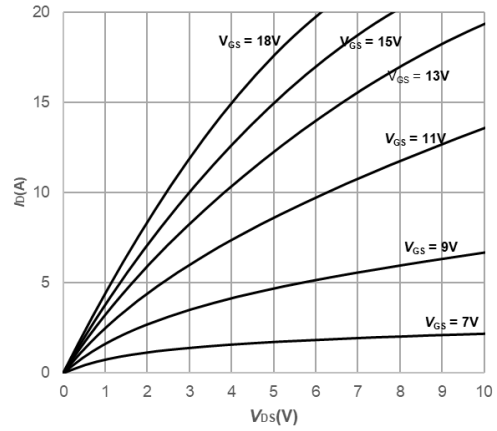


Fig2. Output Characteristics $T_j = 175^{\circ}\text{C}$

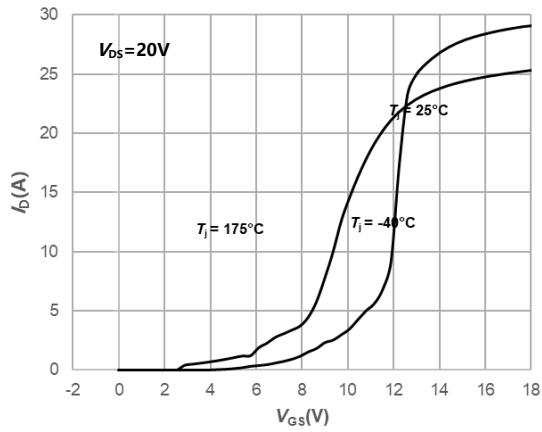


Fig3. Typical Transfer Characteristics

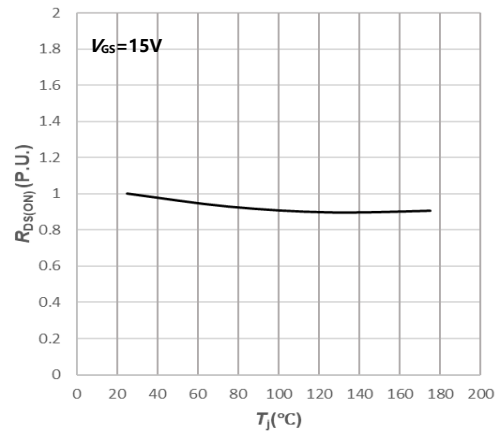


Fig4. Normalized On-Resistance vs. Temperature

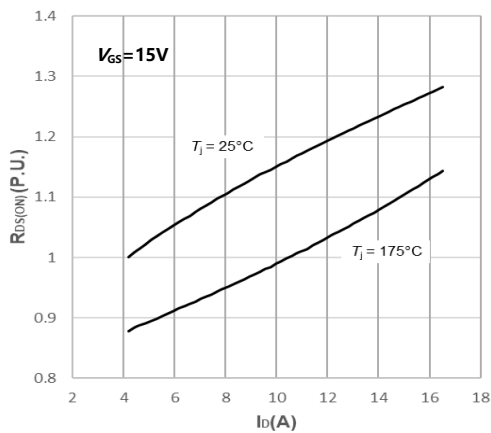


Fig5. Normalized On-Resistance vs. Drain Current For Various Temperatures

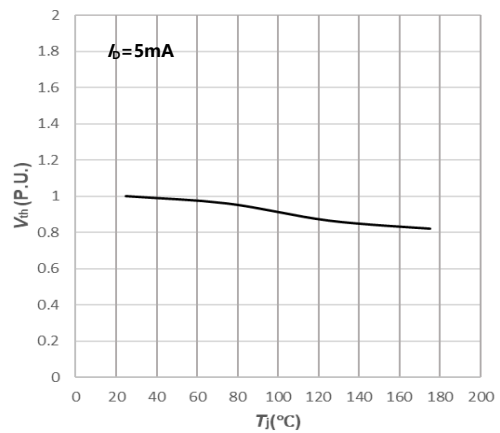


Fig6. Normalized Threshold Voltage vs. Temperature



Typical Performance

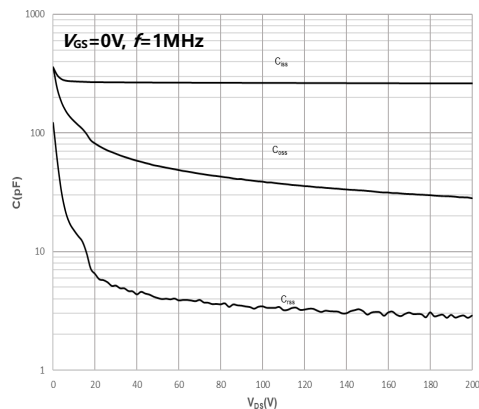


Fig7. Capacitances vs. Drain-Source Voltage (0-200V)

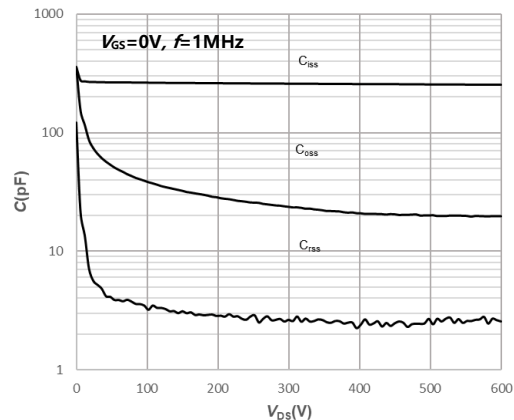


Fig8. Capacitances vs. Drain-Source Voltage (0-600V)

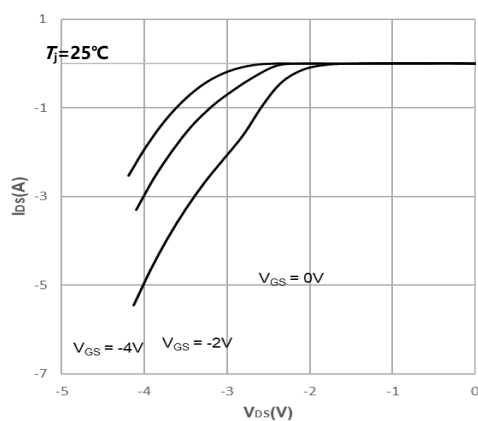
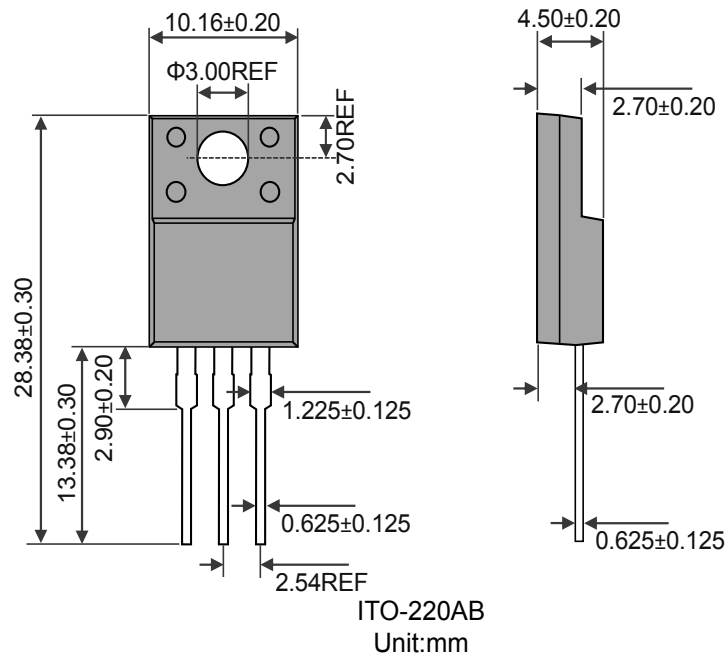


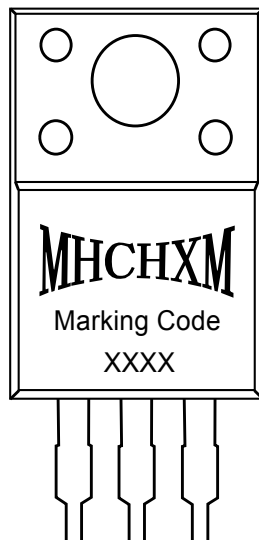
Fig9. Body Diode Characteristics



Package Outline Dimensions



Marking Information



“MHCHXM”= Product Logo

“Marking Code”= The Following

“XXXX”= Date Code Marking

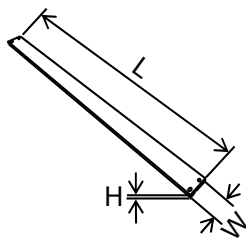
Marking Code	Part Number
C65N250F1	HXMC65N250F1



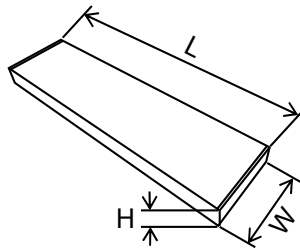
Packing Information

Packaging	Part Number	Quantity(pcs)	Size(mm)
Tube	Tube	50	L534×W33×H7
	Inner Box	1000	L560×W150×H40
	Outer Box	5000	L580×W235×H175

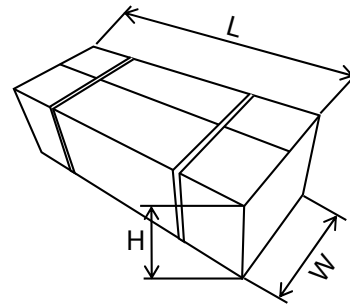
Packaging:Tube



Tube



Tube Inner Box



Tube Outer Box



DISCLAIMER

1. Above specification may be changed without notice. MHCHXM will reserve authority on material change for above specification.
2. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
3. When using this product, please observe the absolute maximum ratings and the instructions for use outlined in these specification sheets. MHCHXM assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
4. These specification sheets include materials protected under copyright of MHCHXM. Reproduction in any form is prohibited without the specific consent of MHCHXM.
5. This product is not intended to be used for military, aircraft, automotive, medical, life sustaining or life saving applications or any other application which can result in human injury or death. Please contact authorized MHCHXM sales agent for special application request.
6. Statements regarding the suitability of products for certain types of applications are based on MHCHXM's knowledge of typical requirements that are often placed on MHCHXM products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify MHCHXM's terms and conditions of purchase, including but not limited to the warranty expressed therein.
7. This publication supersedes & replaces all information previously supplied. For additional application information, please visit our website <http://www.jshxm.com> , or consult your nearest MHCHXM's sales office for further assistance.

